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### N-Channel 650 V (D-S) MOSFET

# PRODUCT SUMMARY $V_{DS}$ (V) $R_{DS(on)}$ (mΩ)(Typ.) $I_D$ (A) a $Q_g$ (Typ.) 650 700 at $V_{GS} = 10 \text{ V}$ 12 37.2nC

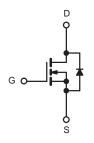
#### **FEATURES**

- DT-Trench Power MOSFET
- $\bullet\,$  100 %  $R_g$  and UIS Tested
- High Input Resistance
- · Excellent FoM (figure of merit)

# RoHS

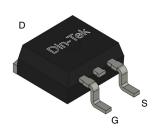
#### **APPLICATIONS**

- · Electronic Ballast
- · Electronic Transformer
- · Switch Mode Power Supply



N-Channel MOSFET

# TO-263 Pin Configuration Top View



ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	LIMIT	UNIT				
Drain-Source Voltage	V <sub>DS</sub>	650	V				
Gate-Source Voltage	$V_{GS}$	± 30					
Continuous Drain Current (T <sub>.I</sub> = 150 °C) <sup>a</sup>	T <sub>C</sub> = 25 °C	L	12	А			
Continuous Drain Current (1) = 150 °C) <sup>a</sup>	T <sub>C</sub> = 100 °C	l <sub>D</sub>	7.7				
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	48					
Single Avalanche Energy	E <sub>AS</sub>	600	mJ				
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	126	W			
waximum rower bissipation	T <sub>C</sub> = 100 °C	T P	50.5				
Operating Junction and Storage Temperature R	T <sub>J</sub> , T <sub>stg</sub>	-55 to+150	°C				

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) <sup>d</sup>	$R_{thJA}$	62.5	°C/W			
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.99	*C/vv			

#### Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c.  $\,$  Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>0JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



<b>SPECIFICATIONS</b> $(T_J = 25  ^{\circ}C,$	unless othe	erwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	650	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.0	-	4.0		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 30 \text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V		-	1		
	I <sub>DSS</sub>	V <sub>DS</sub> = 520 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	12	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.0 A	=	700	900	mΩ	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 5.0 \text{ A}$	-	12.8	-	S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		-	1700	-	pF	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz	-	178	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	8	-		
Total Gate Charge <sup>c</sup>	Qg		-	37.2	-	nC	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>DS</sub> = 520 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	-	7.6	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	12.2	-		
Gate Resistance	$R_g$	f = 1 MHz	1	5.4	-	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	18	-		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 325 \text{ V}, I_D = 10 \text{ A}, R_g = 25\Omega$	-	36	-	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		-	50	-		
Fall Time <sup>c</sup>	t <sub>f</sub>		-	30	-		
Drain-Source Body Diode Ratings and	Characterist	ics <sup>b</sup> (T <sub>J</sub> = 25 °C)		<u>.                                      </u>			
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	12	А	
Pulsed Current	I <sub>SM</sub>		-	-	48	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	-	1.4	V	
Reverse Recovery Time	t <sub>rr</sub>	L _ 10 A di/dt = 100 A/via	-	420	-	ns	
Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 10 \text{ A}, \text{ di/dt } = 100 \text{ A/}\mu\text{s}$	-	4.2	-	μC	

#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.



#### TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

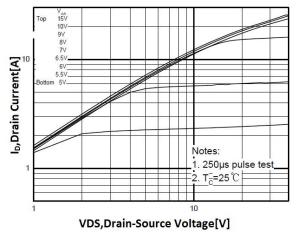
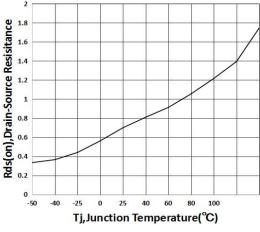


Fig1 Typical Output Characteristics, Tc=25°C

Fig2 On-Resistance Vs.Drain Current and Gate Voltage





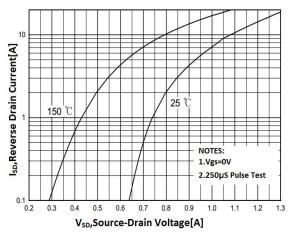
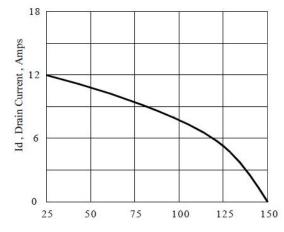
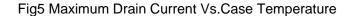


Fig4 Typical Source-Drain Diode Forward Voltage





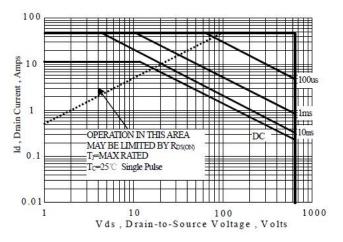
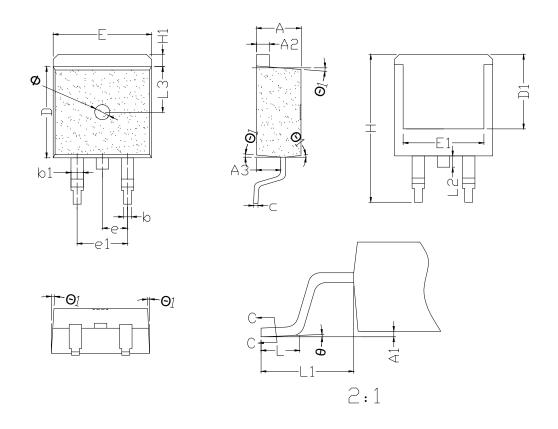


Fig6 Maximum Safe Operating Area



## **TO-263 PACKAGE OUTLINE**



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
Α	4.10	4.50	4.80	е	2.35	2.54	2.75
A1	0.00	0.10	0.30	e1	5.08REF		
A2	1.10	1.30	1.50	Н	14.50	15.15	16.00
А3	2.15	2.50	3.10	H1	1.00	1.28	1.75
b	0.60	0.80	1.05	L	1.80	2.23	2.90
b1	1.05	1.33	1.50	L1	4.30	4.75	5.50
С	0.33	0.50	0.66	L2	1.00	1.30	1.85
D	8.40	9.20	9.60	L3	0.90	4.65	9.00
D1		7.50REF		ф	0°	2°	5°
Е	9.60	10.02	10.80	ф1	2°	-	7°
E1	7.60	9.88	10.30	Ф		1.5BSC	- '





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